

### CLAIMS

1. A method of shaping a piezoelectric material, comprising the steps of:  
depositing a resist mask directly to or through a film for  
amplification of an etching ratio to a surface of an piezoelectric material;  
reforming the resist mask to a predetermined thickness profile; and  
dry etching the piezoelectric material together with the resist mask,  
wherein the piezoelectric material and the resist mask are etched at  
an etching rate different from each other, thereby the surface of the  
piezoelectric material being shaped to a three-dimensional configuration  
corresponding to the thickness profile of the resist mask.
2. The method defined in Claim 1, wherein the thickness profile is  
given to the resist mask by patterning and melting a masking material  
applied to the surface of the piezoelectric material.
3. The method defined in Claim 1, wherein the thickness profile is  
given to the resist mask by pressing a precision stamp onto a masking  
material applied to the surface of the piezoelectric material.
4. The method defined in either one of Claims 1 to 3, wherein the dry  
etching is started with a less selectively reactive gas for reforming the  
resist mask to a predetermined thickness profile and then continued with  
an etching gas having high selective reactivity to the piezoelectric  
material.